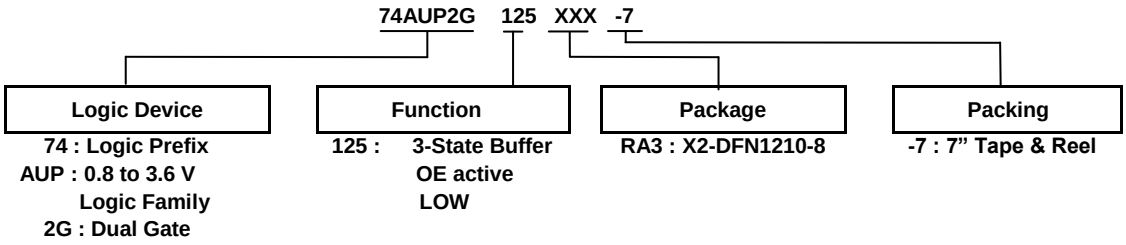
Ordering Information



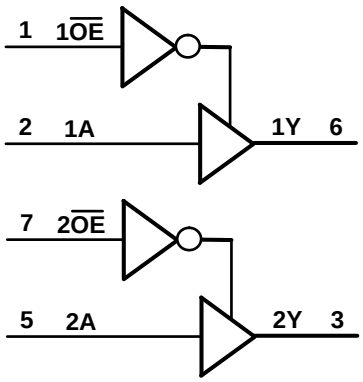
Device	Package Code	Package (Notes 4 & 5)	Package Size	7" Tape and Reel	
				Quantity	Part Number Suffix
74AUP2G125RA3-7	RA3	X2-DFN1210-8	1.2mm X 1.0 mm X 0.35mm 0.3 mm lead pitch	5,000/Tape & Reel	-7

Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
5. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf

Pin Descriptions

Pin Name	Pin NO.	Description
1$\overline{OE}$	1	Output Enable active LOW
1A	2	Data Input
2Y	3	Data Output
GND	4	Ground
2A	5	Data Input
1Y	6	Data Output
2$\overline{OE}$	7	Output Enable active LOW
V_{CC}	8	Supply Voltage

Logic Diagram



Function Table

Inputs		Output
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V_{CC}	Supply Voltage Range	-0.5 to +4.6	V
V_I	Input Voltage Range	-0.5 to +4.6	V
V_o	Voltage Applied to Output in High or Low State	-0.5 to V_{CC} +0.5	V
I_{IK}	Input Clamp Current $V_I < 0$	50	mA
I_{OK}	Output Clamp Current ($V_O < 0$)	50	mA
I_O	Continuous Output Current (V_O = 0 to V_{CC})	±20	mA
I_{CC}	Continuous Current Through V_{CC}	50	mA
I_{GND}	Continuous Current Through GND	-50	mA
T_J	Operating Junction Temperature	-40 to +150	°C
T_{STG}	Storage Temperature	-65 to +150	°C

Notes: 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.
7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

Recommended Operating Conditions (Note 8)

Symbol	Parameter		Min	Max	Unit
V_{CC}	Operating Voltage		0.8	3.6	V
V_I	Input Voltage		0	3.6	V
V_O	Output Voltage		0	V_{CC}	V
I_{OH}	High-Level Output Current	V_{CC} = 0.8V	—	-20	µA
		V_{CC} = 1.1V	—	-1.1	mA
		V_{CC} = 1.4V	—	-1.7	
		V_{CC} = 1.65V	—	-1.9	
		V_{CC} = 2.3V	—	-3.1	
		V_{CC} = 3.0V	—	-4	
I_{OL}	Low-Level Output Current	V_{CC} = 0.8V	—	20	µA
		V_{CC} = 1.1V	—	1.1	mA
		V_{CC} = 1.4V	—	1.7	
		V_{CC} = 1.65V	—	1.9	
		V_{CC} = 2.3V	—	3.1	
		V_{CC} = 3.0V	—	4	
Δt/ΔV	Input Transition Rise or Fall Rate	V_{CC} = 0.8V to 3.6V	—	200	ns/V
T_A	Operating Free-Air Temperature		-40	125	°C

Note: 8. Unused inputs should be held at V_{CC} or Ground.

Electrical Characteristics

Symbol	Parameter	Test Conditions	V_{CC}	T_A = +25°C		T_A = -40°C to +85°C		Unit
				Min	Max	Min	Max	
V_{IH}	High-Level Input Voltage	—	0.8V to 1.65V	0.80 X V_{CC}	—	0.80 X V_{CC}	—	V
		—	1.65V to 1.95V	0.65 X V_{CC}	—	0.65 X V_{CC}	—	
		—	2.3V to 2.7V	1.6	—	1.6	—	
		—	3.0V to 3.6V	2.0	—	2.0	—	
V_{IL}	Low-Level Input Voltage	—	0.8V to 1.65V	—	0.30 X V_{CC}	—	0.30 X V_{CC}	V
		—	1.65V to 1.95V	—	0.35 X V_{CC}	—	0.35 X V_{CC}	
		—	2.3V to 2.7V	—	0.7	—	0.7	
		—	3.0V to 3.6V	—	0.9	—	0.9	
V_{OH}	High-Level Output Voltage	I_{OH} = -20μA	0.8V to 3.6V	V_{CC} – 0.1	—	V_{CC} – 0.1	—	V
		I_{OH} = -1.1mA	1.1V	0.75 X V_{CC}	—	0.7 X V_{CC}	—	
		I_{OH} = -1.7mA	1.4V	1.11	—	1.03	—	
		I_{OH} = -1.9mA	1.65V	1.32	—	1.3	—	
		I_{OH} = -2.3mA	2.3V	2.05	—	1.97	—	
		I_{OH} = -3.1mA		1.9	—	1.85	—	
		I_{OH} = -2.7mA	3V	2.72	—	2.67	—	
		I_{OH} = -4mA		2.6	—	2.55	—	
V_{OL}	Low-Level Output Voltage	I_{OL} = 20μA	0.8V to 3.6V	—	0.1	—	0.1	V
		I_{OL} = 1.1mA	1.1V	—	0.3 X V_{CC}	—	0.3 X V_{CC}	
		I_{OL} = 1.7mA	1.4V	—	0.31	—	0.37	
		I_{OL} = 1.9mA	1.65V	—	0.31	—	0.35	
		I_{OL} = 2.3mA	2.3V	—	0.31	—	0.33	
		I_{OL} = 3.1mA		—	0.44	—	0.45	
		I_{OL} = 2.7mA	3V	—	0.31	—	0.33	
		I_{OL} = 4mA		—	0.44	—	0.45	
I_I	Input Current	A or B Input V_I = GND to 3.6V	0 to 3.6V	—	± 0.1	—	± 0.5	μA
I_{OZ}	Z-State Leakage Current	V_I or V_O = 0V to 3.6V	0 to 3.6V	—	0.2	—	± 0.5	μA
I_{OFF}	Power Down Leakage Current	V_I or V_O = 0V to 3.6V	0 V		± 0.2		± 0.5	μA
ΔI_{OFF}	Delta Power Down Leakage Current	V_I or V_O = 0V to 3.6V	0 V to 0.2V	—	0.2	—	0.6	μA
I_{CC}	Supply Current	V_I = GND or V_{CC}, I_O = 0	0.8 V to 3.6V	—	0.5	—	0.9	μA
ΔI_{CC}	Additional Supply Current	Data Input at V_{CC} –0.6 V OE= GND I_O=0 A	3.3V	—	40	—	50	μA
		OE Input at VCC –0.6 V Data Input= GND or Vcc I_O=0 A	3.3V	—	110	—	120	μA
		OE Input at VCC Data Input= GND to 3.6 V I_O=0 A	0.8V to 3.6V	—	1	—	1	μA

Electrical Characteristics (cont.)

Symbol	Parameter	Test Conditions	V_{CC}	T_A = -40°C to +125°C		Unit
				Min	Max	
V_{IH}	High-Level Input Voltage	—	0.8V to 1.65V	0.80 X V_{CC}	—	V
		—	1.65V to 1.95V	0.70 X V_{CC}	—	
		—	2.3V to 2.7V	1.6	—	
		—	3.0V to 3.6V	2.0	—	
V_{IL}	Low-Level Input Voltage	—	0.8V to 1.65V	—	0.25 X V_{CC}	V
		—	1.65V to 1.95V	—	0.30 X V_{CC}	
		—	2.3V to 2.7V	—	0.7	
		—	3.0V to 3.6V	—	0.9	
V_{OH}	High-Level Output Voltage	I_{OH} = -20µA	0.8V to 3.6V	V_{CC} – 0.11	—	V
		I_{OH} = -1.1mA	1.1V	0.6 X V_{CC}	—	
		I_{OH} = -1.7mA	1.4V	0.93	—	
		I_{OH} = -1.9mA	1.65V	1.17	—	
		I_{OH} = -2.3mA	2.3V	1.77	—	
		I_{OH} = -3.1mA		1.67	—	
		I_{OH} = -2.7mA	3V	2.40	—	
		I_{OH} = -4mA		2.30	—	
V_{OL}	Low-Level Output Voltage	I_{OL} = 20µA	0.8V to 3.6V	—	0.11	V
		I_{OL} = 1.1mA	1.1V	—	0.33 X V_{CC}	
		I_{OL} = 1.7mA	1.4V	—	0.41	
		I_{OL} = 1.9mA	1.65V	—	0.39	
		I_{OL} = 2.3mA	2.3V	—	0.36	
		I_{OL} = 3.1mA		—	0.50	
		I_{OL} = 2.7mA	3V	—	0.36	
		I_{OL} = 4mA		—	0.50	
I_I	Input Current	A or B Input, V_I = GND to 3.6V	0 to 3.6V	—	± 0.75	µA
I_{OZ}	Z-State Leakage Current	V_I or V_O = 0V to 3.6V	0 to 3.6V	—	± 1.5	µA
I_{OFF}	Power Down Leakage Current	V_I or V_O = 0V to 3.6V	0	—	± 3.5	µA
ΔI_{OFF}	Delta Power Down Leakage Current	V_I or V_O = 0V to 3.6V	0V to 0.2V	—	± 2.5	µA
I_{CC}	Supply Current	V_I = GND or V_{CC}, I_O = 0	0.8V to 3.6V	—	3.0	µA
ΔI_{CC}	Additional Supply Current	Data Input at V_{CC} –0.6 V OE= GND I_O=0 A	3.3V	—	75	µA
		OE Input at VCC –0.6 V Data Input= GND or Vcc I_O=0 A	3.3V	—	180	µA
		OE Input at VCC Data Input= GND to 3.6 V I_O=0 A	0.8V to 3.6V	—	1	µA

Operating and Package Characteristics (@T_A = +25°C, unless otherwise specified.)

Parameter		Test Conditions		V_{CC}	Typ	Unit
C_{pd}	Power Dissipation Capacitance per gate	f = 1MHz Output Enabled No Load		0.8V	6.5	pF
				1.2V ± 0.1V	6.3	
				1.5V ± 0.1V	6.3	
				1.8V ± 0.15V	6.2	
				2.5V ± 0.2V	6.2	
				3.3V ± 0.3V	6.1	
C_i	Input Capacitance	V_i = V_{CC} or GND		0V or 3.3V	1.5	pF
C_O	Output Capacitance	Output Enabled VO=Gnd		0 V	2.9	pF
		Output Disabled VO=Gnd or Vcc		0V or 3.6V	2.1	pF
θ_{JA}	Thermal Resistance Junction-to-Ambient	X2-DFN1210-8	(Note 9)	—	395	°C/W
θ_{JC}	Thermal Resistance Junction-to-Case	X2-DFN1210-8	(Note 9)	—	236	°C/W

Note: 9. Test condition, X2-DFN1210-8 device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Switching Characteristics

C_L = 5pF, See Figure 1

Parameter	From Input	To Output	V_{CC}	T_A = +25°C			T_A = -40°C to +85°C		T_A = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{pd}	A	Y	0.8V	—	20.6	—	—	—	—	—	ns
			1.2V ± 0.1V	2.8	5.5	12.6	2.5	14.0	2.5	17	
			1.5V ± 0.1V	2.2	3.9	7.3	2.0	7.5	2.0	8.1	
			1.8V ± 0.15V	1.9	3.2	4.8	1.7	6.1	1.7	6.7	
			2.5V ± 0.2V	1.6	2.6	3.6	1.4	4.3	1.4	4.9	
			3.3V ± 0.3V	1.4	2.4	3.1	1.2	3.9	1.2	4.4	
t_{en}	$\overline{OE}$	Y	0.8V	—	69.9	—	—	—	—	—	ns
			1.2V ± 0.1V	3.1	6.1	14.2	2.9	20	2.9	22.2	
			1.5V ± 0.1V	2.5	4.2	7.9	2.3	9.2	2.3	10.0	
			1.8V ± 0.15V	2.1	3.4	6.1	2.0	7.4	2.0	8.2	
			2.5V ± 0.2V	1.8	2.6	4.4	1.7	5.4	1.7	6.0	
			3.3V ± 0.3V	1.7	2.4	4.0	1.7	4.6	1.7	5.1	
t_{dis}	$\overline{OE}$	Y	0.8V	—	14.3	—	—	—	—	—	ns
			1.2V ± 0.1V	2.7	4.3	9.4	2.7	10.6	2.7	11.8	
			1.5V ± 0.1V	2.1	3.2	6.4	2.1	7.3	2.1	8.2	
			1.8V ± 0.15V	2.0	3.0	5.5	2.0	6.3	2.0	7.1	
			2.5V ± 0.2V	1.4	2.2	3.7	1.4	4.2	1.4	5.1	
			3.3V ± 0.3V	1.7	2.5	4.4	1.7	4.6	1.7	5.4	

C_L = 10pF, See Figure 1

Parameter	From Input	To Output	V_{CC}	T_A = +25°C			T_A = -40°C to +85°C		T_A = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{pd}	A	Y	0.8V	—	24.0	—	—	—	—	—	ns
			1.2V ± 0.1V	3.2	6.4	14.8	3.0	16.6	3.0	18.2	
			1.5V ± 0.1V	2.1	4.5	8.8	1.9	9.1	1.9	9.4	
			1.8V ± 0.15V	1.9	3.8	5.5	1.7	6.8	1.7	7.6	
			2.5V ± 0.2V	2.1	3.2	4.2	1.6	5.3	1.6	5.9	
			3.3V ± 0.3V	1.8	3.0	3.8	1.6	4.6	1.6	5.2	
t_{en}	$\overline{OE}$	Y	0.8V	—	73.7	—	—	—	—	—	ns
			1.2V ± 0.1V	3.6	6.9	16.2	3.4	22.8	3.4	25.2	
			1.5V ± 0.1V	2.3	4.8	9.2	2.2	10.3	2.2	11.3	
			1.8V ± 0.15V	2.0	3.9	7.0	1.9	8.2	1.9	8.9	
			2.5V ± 0.2V	1.8	3.2	5.2	1.7	6.4	1.7	7.1	
			3.3V ± 0.3V	1.7	3.0	5.1	1.7	5.6	1.7	6.2	
t_{dis}	$\overline{OE}$	Y	0.8V	—	32.7	—	—	—	—	—	ns
			1.2V ± 0.1V	3.4	5.4	11.4	3.4	12.7	3.4	14.3	
			1.5V ± 0.1V	2.2	4.1	7.9	2.2	8.9	2.2	10.2	
			1.8V ± 0.15V	2.2	4.2	7.0	1.9	8.0	1.9	8.9	
			2.5V ± 0.2V	1.7	3.0	4.8	1.7	5.7	1.7	6.4	
			3.3V ± 0.3V	2.1	3.8	6.5	1.7	6.8	1.7	7.7	

Switching Characteristics (cont.)

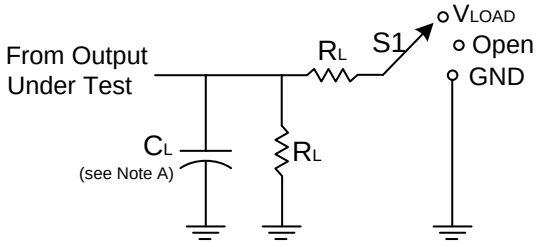
C_L = 15pF, See Figure 1

Parameter	From Input	To Output	V_{CC}	T_A = +25°C			T_A = -40°C to +85°C		T_A = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{pd}	A	Y	0.8V	—	27.4	—	—	—	—	—	ns
			1.2V ± 0.1V	3.6	7.2	15.8	3.3	22.4	3.3	22.5	
			1.5V ± 0.1V	3.0	5.1	8.8	2.5	9.8	2.5	10.9	
			1.8V ± 0.15V	2.2	4.3	6.3	2.0	7.9	2.0	8.8	
			2.5V ± 0.2V	2.0	3.7	4.9	1.8	6.0	1.8	6.7	
			3.3V ± 0.3V	2.0	3.5	4.4	1.8	5.4	1.8	6.1	
t_{en}	$\overline{OE}$	Y	0.8V	—	77.5	—	—	—	—	—	ns
			1.2V ± 0.1V	4.0	7.7	18.2	3.7	21.8	3.7	23.5	
			1.5V ± 0.1V	3.0	5.3	10.1	2.5	11.8	2.5	12.8	
			1.8V ± 0.15V	2.3	4.4	7.8	2.1	9.2	2.1	10.2	
			2.5V ± 0.2V	2.1	3.6	6.0	2.0	7.3	2.0	8.2	
			3.3V ± 0.3V	2.0	3.5	5.7	1.9	6.4	1.9	7.2	
t_{dis}	$\overline{OE}$	Y	0.8V	—	60.8	—	—	—	—	—	ns
			1.2V ± 0.1V	4.3	6.5	13.9	3.7	15.5	3.7	15.7	
			1.5V ± 0.1V	3.0	5.0	8.8	2.5	9.7	2.5	9.8	
			1.8V ± 0.15V	3.0	5.3	8.8	2.1	10.3	2.1	10.5	
			2.5V ± 0.2V	2.1	3.8	8.2	2.0	8.4	2.0	8.6	
			3.3V ± 0.3V	2.9	5.0	8.6	1.9	9.2	1.9	9.4	

C_L = 30pF, See Figure 1

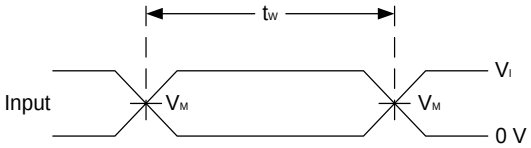
Parameter	From Input	To Output	V_{CC}	T_A = +25°C			T_A = -40°C to +85°C		T_A = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{pd}	A	Y	0.8V	—	37.4	—	—	—	—	—	ns
			1.2V ± 0.1V	4.8	9.5	21	4.4	24.9	4.4	25	
			1.5V ± 0.1V	4.0	6.7	10.8	3.0	13.0	3.0	14.5	
			1.8V ± 0.15V	2.9	5.6	8.4	2.6	10.3	2.6	11.5	
			2.5V ± 0.2V	2.7	4.8	6.3	2.5	7.8	2.5	8.7	
			3.3V ± 0.3V	2.7	4.6	6	2.5	7.5	2.5	8.3	
t_{en}	$\overline{OE}$	Y	0.8V	—	88.9	—	—	—	—	—	ns
			1.2V ± 0.1V	5.2	9.9	23.8	4.8	27.4	4.8	30.4	
			1.5V ± 0.1V	4.0	6.8	13.0	3.1	15.1	3.1	16.9	
			1.8V ± 0.15V	3.0	5.6	10.2	2.8	12.2	2.8	13.6	
			2.5V ± 0.2V	2.7	4.8	7.8	2.6	9.4	2.6	10.6	
			3.3V ± 0.3V	2.7	4.6	7.8	2.6	9.0	2.6	10.0	
t_{dis}	$\overline{OE}$	Y	0.8V	—	49.9	—	—	—	—	—	ns
			1.2V ± 0.1V	6.0	9.9	16.0	4.8	17.8	4.8	19.8	
			1.5V ± 0.1V	4.4	7.7	11.5	3.1	13.0	3.1	14.5	
			1.8V ± 0.15V	5.1	8.7	13.3	2.8	14.9	2.8	16.6	
			2.5V ± 0.2V	3.6	6.2	9.1	2.6	10.3	2.6	11.5	
			3.3V ± 0.3V	5.2	8.7	13.7	2.6	14.0	2.6	17.0	

Parameter Measurement Information

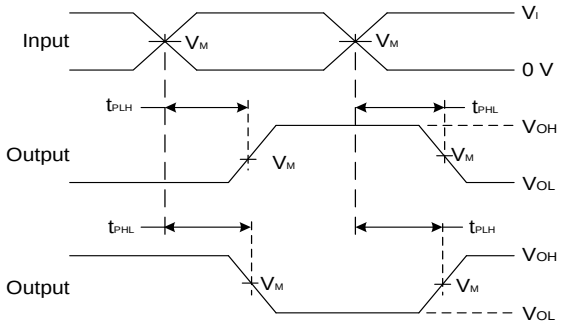


TEST	S1	R_L
t_{PLH}/t_{PHL}	Open	1MΩ
t_{PLZ}/t_{PZL}	Vload	5KΩ
t_{PHZ}/t_{PZH}	GND	5KΩ

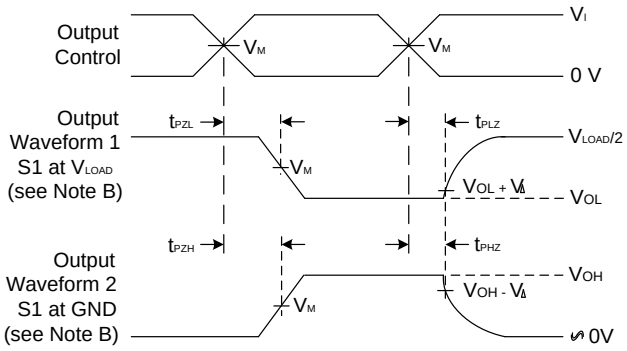
Vcc	Inputs		V_M	V_{LOAD}	C_L	VΔ
	V_I	t_r/t_f				
0.8V	V_{CC}	≤3ns	$V_{CC}/2$	2 X V_{CC}	5, 10, 15, 30pF	0.1 V
1.2V±0.1V	V_{CC}	≤3ns	$V_{CC}/2$	2 X V_{CC}	5, 10, 15, 30pF	0.1 V
1.5V±0.1V	V_{CC}	≤3ns	$V_{CC}/2$	2 X V_{CC}	5, 10, 15, 30pF	0.1 V
1.8V ±0.15V	V_{CC}	≤3ns	$V_{CC}/2$	2 X V_{CC}	5, 10, 15, 30pF	0.15 V
2.5V±0.2V	V_{CC}	≤3ns	$V_{CC}/2$	2 X V_{CC}	5, 10, 15, 30pF	0.15 V
3.3V±0.3V	V_{CC}	≤3ns	$V_{CC}/2$	2 X V_{CC}	5, 10, 15, 30pF	0.3V



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times Low and High Level Enabling

Figure 1 Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.
B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
C. Inputs are measured separately one transition per measurement.
D. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
E. t_{PZL} and t_{PZH} are the same as t_{EN}.
F. t_{PLH} and t_{PHL} are the same as t_{PD}.

Marking Information

X2-DFN1210-8

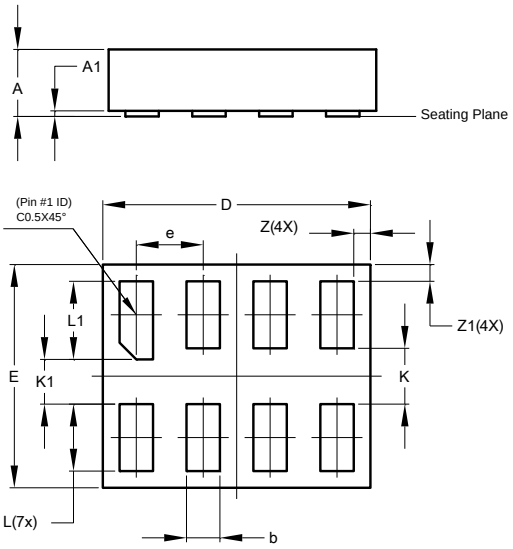
(Top View)

XX : Identification Code
Y : Year : 0~9
W : week : A~Z : 1~26 week
a~z: 27-52 week
z represents 52 and 53 week
X : week : A~Z : Internal code

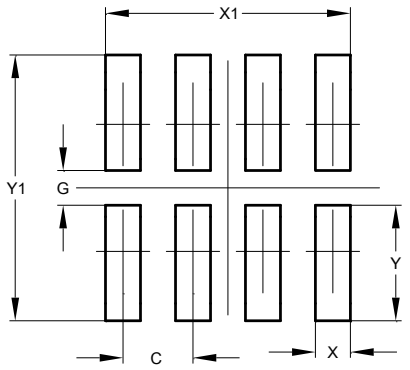
Part Number	Package	Identification Code
74AUP2G125RA3-7	X2-DFN1210-8	JT

X2-DFN1210-8 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X2-DFN1210-8			
Dim	**Min**	**Max**	**Typ**
A	-	0.35	0.30
A1	0	0.03	0.02
b	0.10	0.20	0.15
D	1.15	1.25	1.20
E	0.95	1.05	1.00
e	-	-	0.30
K	-	-	0.25
K1	-	-	0.20
L	0.25	0.35	0.30
L1	0.30	0.40	0.35
Z	0.050	0.100	0.075
Z1	0.050	0.100	0.075
All Dimensions in mm			



Dimensions	Value (in mm)
C	0.300
G	0.150
X	0.150
X1	1.050
Y	0.500
Y1	1.150

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